JMH65R110APLNFD

650V SuperJunction Power MOSFET

Features

- Extremely Low Gate Charge
- Excellent Output Capacitance (C_{oss}) Profile
- Fast Switching Capability
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant
- AEC-Q101 Qualified for Automotive Applications

Product Summary

Parameter	Value	Unit
V_{DS}	650	V
$V_{GS(th)\_Typ}$	3.5	V
I_D (@ V_{GS} = 10V) (1)	32	A
$R_{DS(ON)\_Typ}$ (@ V_{GS} = 10V)	95	mΩ
E_{oss}@400V	7.8	μJ

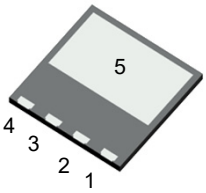
Applications

- Switching Applications

DFN8080-4L

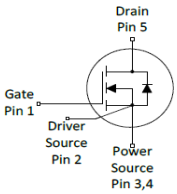
Top View

Bottom View



Pin Configuration

Top View



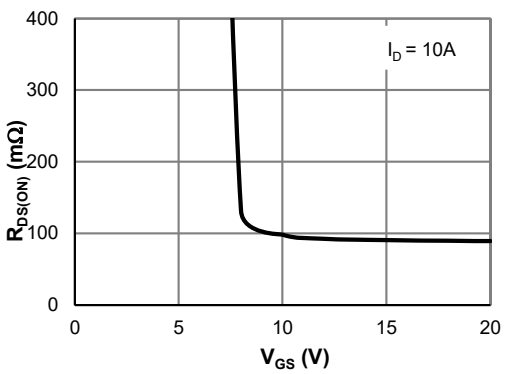
Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMH65R110APLNFD-13	DFN8080-4	4	65R110AF	1	-55 to 150	13-inch Reel	3000

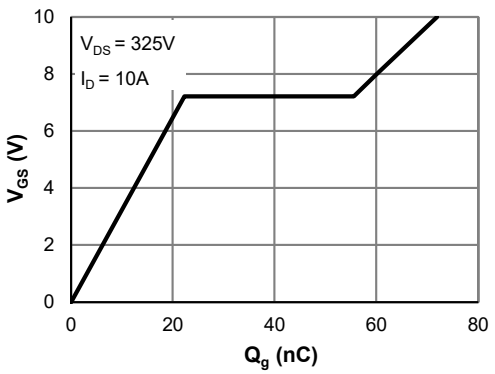
Absolute Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	650	V
Gate-to-Source Voltage		V_{GS}	±30	V
Continuous Drain Current (1)	T_C = 25°C	I_D	32	A
	T_C = 100°C		19.0	
Pulsed Drain Current (2)		I_{DM}	137	A
Avalanche Current (3)		I_{AS}	10.0	A
Avalanche Energy (3)		E_{AS}	500	mJ
Power Dissipation (4)	T_C = 25°C	P_D	250	W
	T_C = 100°C		100	
Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

$R_{DS(ON)}$ vs. V_{GS}



Gate Charge



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Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = 250μA, V_{GS} = 0V	650			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V			10.0	μA
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±30V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	3.5	4.5	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 10A		95	110	mΩ
Diode Forward Voltage	V_{SD}	I_S = 1A, V_{GS} = 0V		0.75		V
Diode Continuous Current	I_S	T_C = 25°C			10	A
DYNAMIC PARAMETERS (5)						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 100V, f = 1MHz		2869		pF
Output Capacitance	C_{oss}			93		pF
Effective output capacitance, energy related	$C_{o(er)}$	V_{GS}=0V, V_{DS}=0...400V		97		pF
Effective output capacitance, time related	$C_{o(tr)}$	ID=constant, V_{GS}=0V, V_{DS}=0...400V		410		pF
Reverse Transfer Capacitance	C_{rss}	V_{GS} = 0V, V_{DS} = 100V, f = 1MHz		5.4		pF
Gate Resistance	R_g	f = 1MHz		2.2		Ω
SWITCHING PARAMETERS (5)						
Total Gate Charge (@ V_{GS} = 10V)	Q_g	V_{GS} = 0 to 10V V_{DS} = 325V, I_D = 10A		72		nC
Gate Source Charge	Q_{gs}			22		nC
Gate Drain Charge	Q_{gd}			33		nC
Turn-On DelayTime	$t_{D(on)}$	V_{GS} = 10V, V_{DS} = 325V R_L = 32.5Ω, R_{GEN} = 6Ω		29		ns
Turn-On Rise Time	t_r			30		ns
Turn-Off DelayTime	$t_{D(off)}$			77		ns
Turn-Off Fall Time	t_f			17.4		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10A, dI_F/dt = 100A/μs		152		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F = 10A, dI_F/dt = 100A/μs		2.5		μC
Peak Diode Recovery Voltage Slope	dv/dt	I_F≤2A, di/dt = 200A/us, V_{DS} = 400V		15.0		V/ns
MOSFET dv/dt Ruggedness	dv/dt	V_{DS} = 0...400V		50		V/ns

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	47	58	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.50	0.60	°C/W

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under T_{J_Max} = 150°C.
3. This single-pulse measurement was taken under the following condition [L = 10mH, V_{GS} = 10V, V_{DD} = 50V] while its value is limited by T_{J_Max} = 150°C.
4. The power dissipation P_D is based on T_{J_Max} = 150°C.
5. This value is guaranteed by design hence it is not included in the production test.

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Typical Electrical & Thermal Characteristics

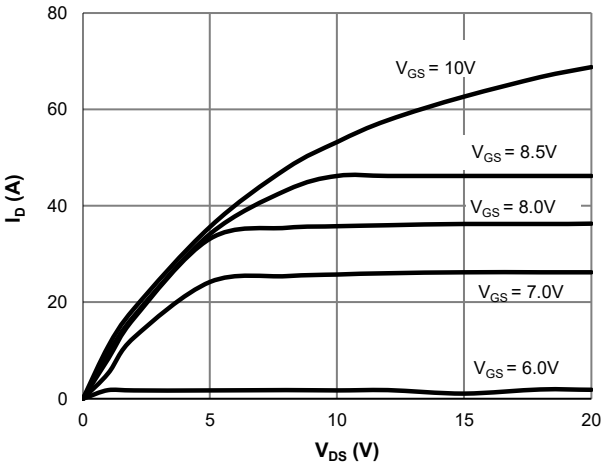

Figure 1: Saturation Characteristics

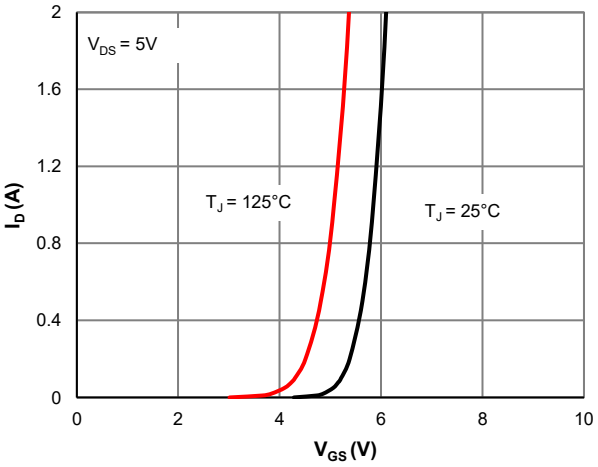

Figure 2: Transfer Characteristics

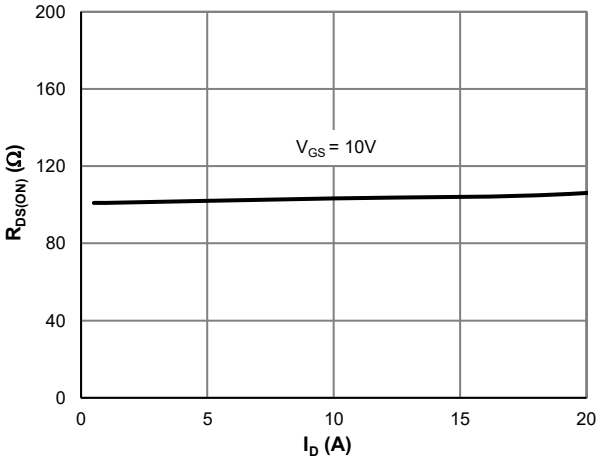

Figure 3: $R_{DS(ON)}$ vs. Drain Current

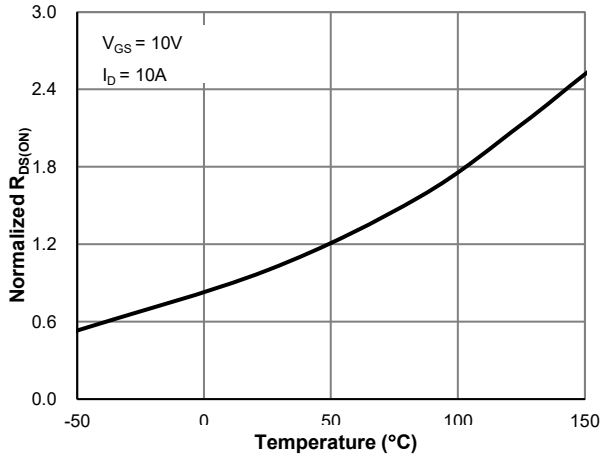

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

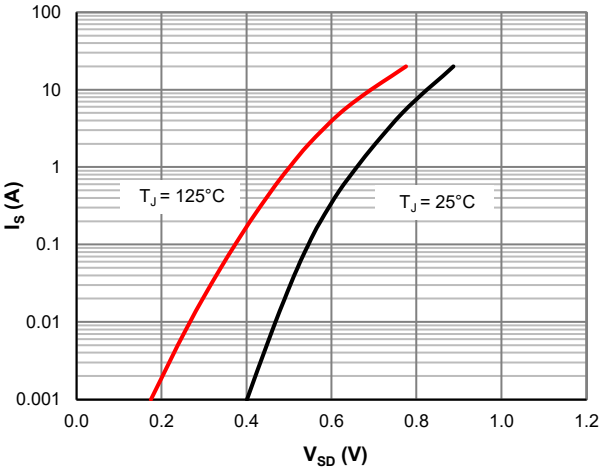

Figure 5: Body-Diode Characteristics

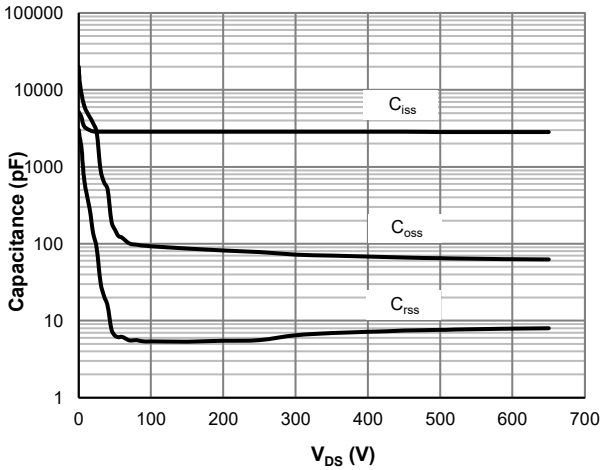

Figure 6: Capacitance Characteristics

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Typical Electrical & Thermal Characteristics

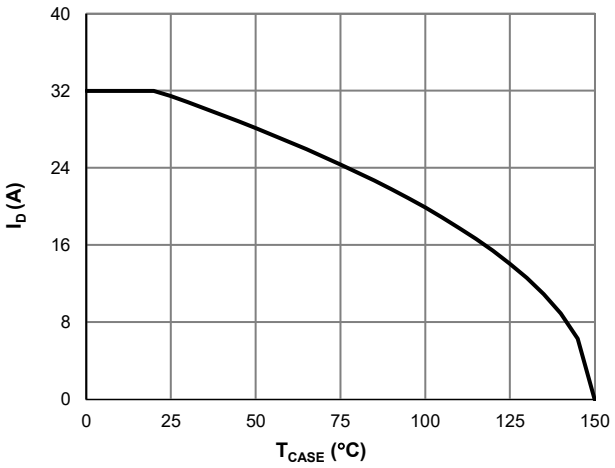

Figure 7: Current De-rating

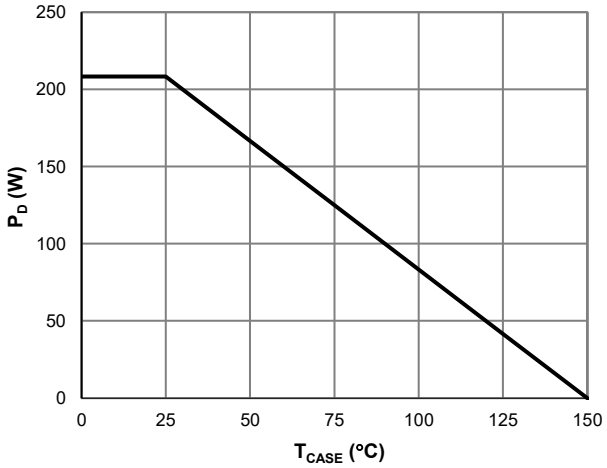

Figure 8: Power De-rating

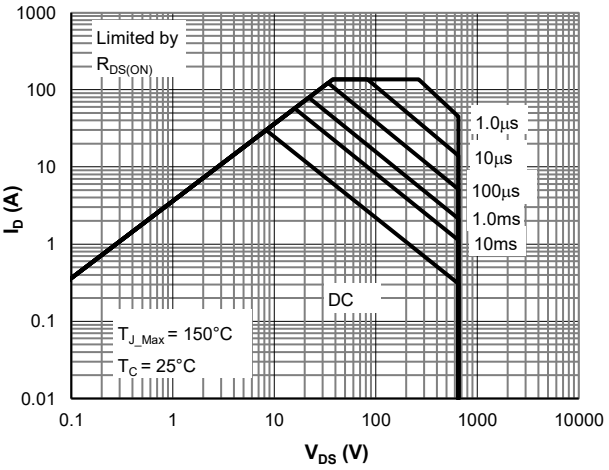

Figure 9: Maximum Safe Operating Area

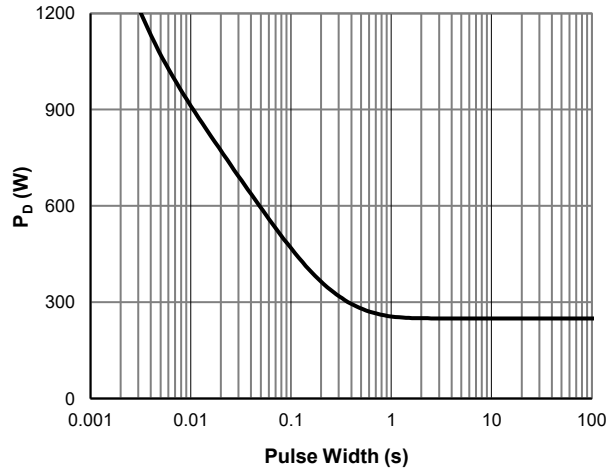

Figure 10: Single Pulse Power Rating, Junction-to-Case

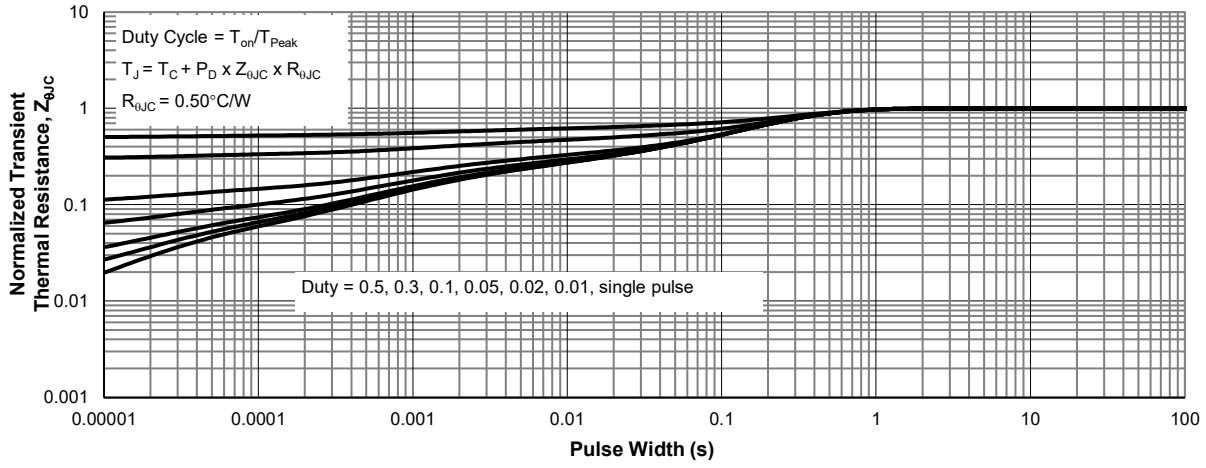

Figure 11: Normalized Maximum Transient Thermal Impedance

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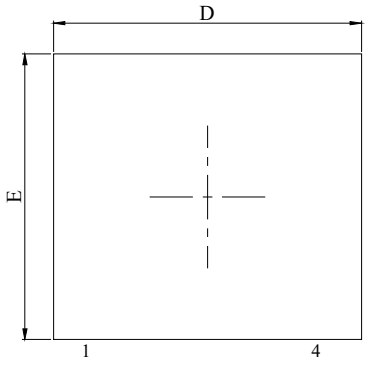
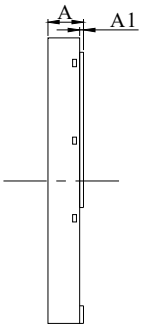
DFN8080-4L Package Information

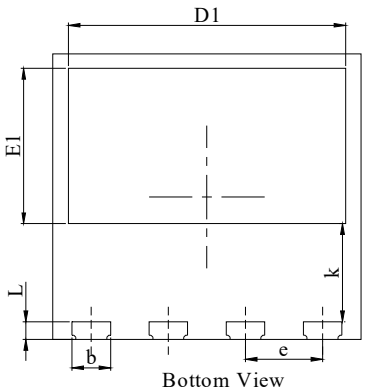
Package Outlines



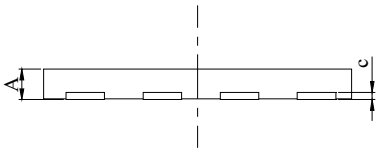
Top View



Side View



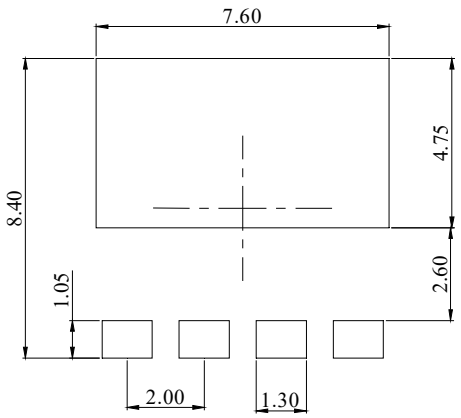
Bottom View



Front View

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.85	0.90	0.95
A1	--	--	0.05
b	0.95	1.00	1.05
c	--	0.20	--
D	7.90	8.00	8.10
D1	7.10	7.20	7.30
E	7.90	8.00	8.10
E1	4.25	4.35	4.45
L	0.40	0.50	0.60
k	2.75		
e	2.00 BSC		

Recommended Soldering Footprint



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